



ACGI053059-P46

C-band matched GaAs Device

Features:

Frequency: 5.3~5.9GHz

Saturated Output Power : $P_{Sat}=46\text{dBm}(\text{type})$

PowerGain: Gain=8.5dB(type)

Add-Efficiency: PAE=35%(type)

Port matching: $Z_{in}/Z_{out}=50\Omega$

Description:

ACGI053059-P46 is an internal matching GaAs device, which adopts advanced co-planar internal matching MCM and thin film circuit technology. The typical working frequency range is 5.3~5.9GHz. This device can be used in different RF/Microwave system and subsystem. The high output power level, high efficiency and wide operating temperature range can make application very flexible.

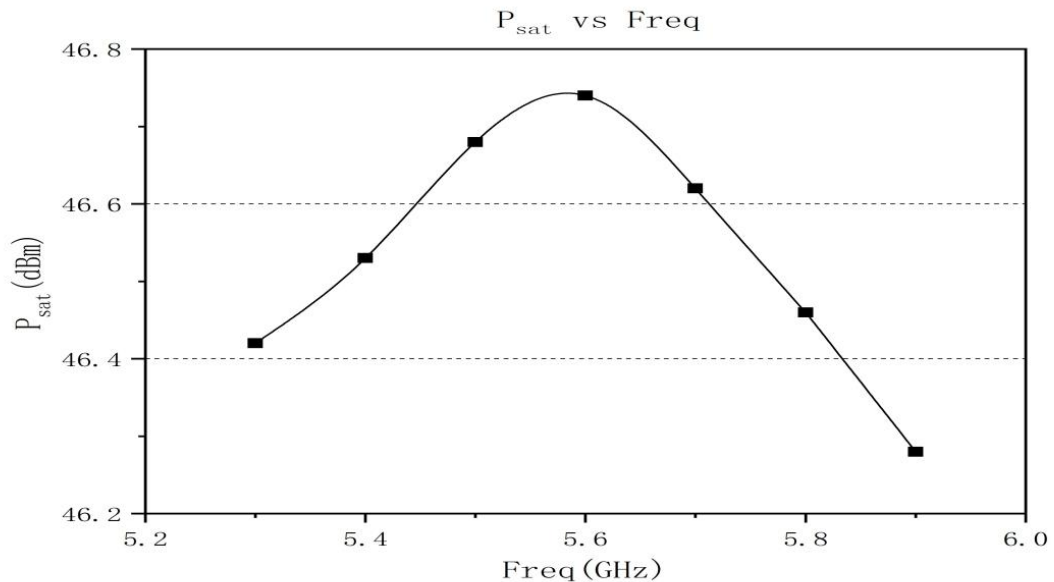
Maximun Ratings (TC=25°C, Not recommended working under this condition):

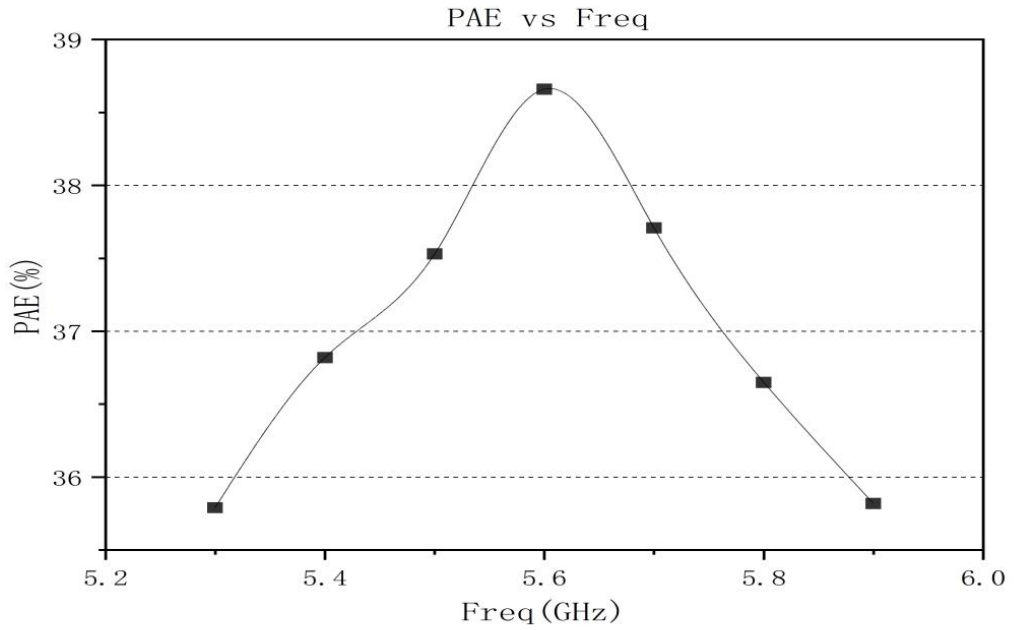
| | Symbol | Value | Unit |
|--------------------------------------|-----------|-------------|------|
| Voltage between source and drain | V_{ds} | 11 | V |
| Voltage between gate and source | V_{gs} | -3 | V |
| Storage Temperature Range | T_{stg} | -65 to +150 | °C |
| Drain and Source Channel Temperature | T_{ch} | 150 | °C |

Electrical Characteristics:

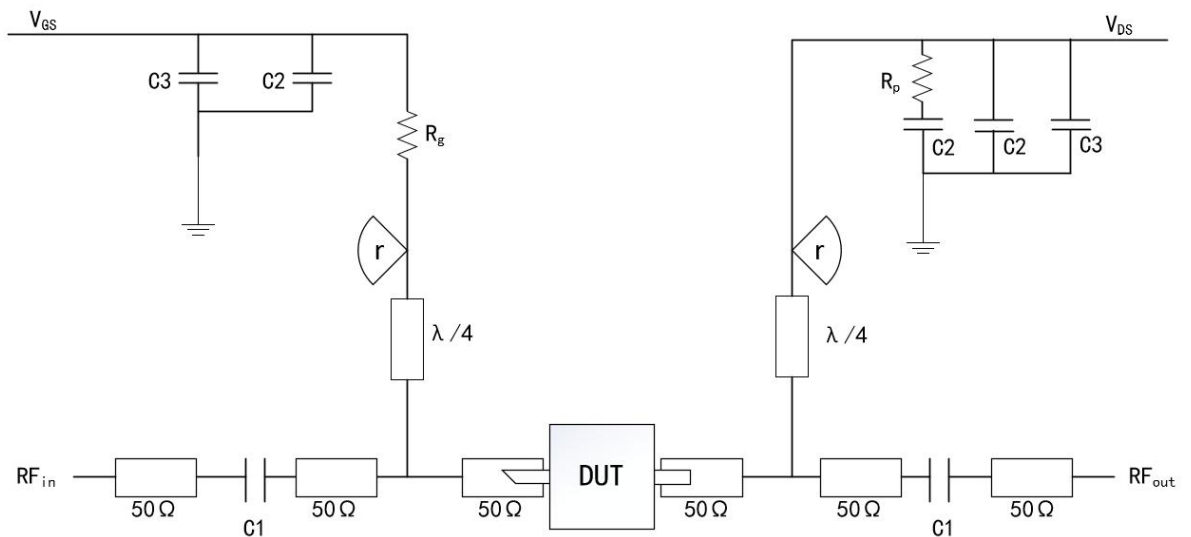
| | Symbol | Test condition | Value | | | Unit |
|------------------------|------------------|---|-------|-----|------|------|
| | | | Min | Typ | Max | |
| Drain Current | I _{dsr} | V _{ds} =10V CW. P _{in} : 37.5dBm Freq: 5.3~5.9GHz | - | 9.8 | - | A |
| Saturated output power | P _{sat} | | - | 46 | - | dBm |
| Gain | G _p | | - | 8.5 | - | dB |
| Add-Efficiency | PAE | | - | 35 | - | % |
| Gain Flatness | ΔG | | -0.8 | - | +0.8 | dB |

Typical Curve:





Application Circuit:



DUT: Device to be tested

C1:4.7pF

C2:1000pF

C3:100uF

R_p:51Ω

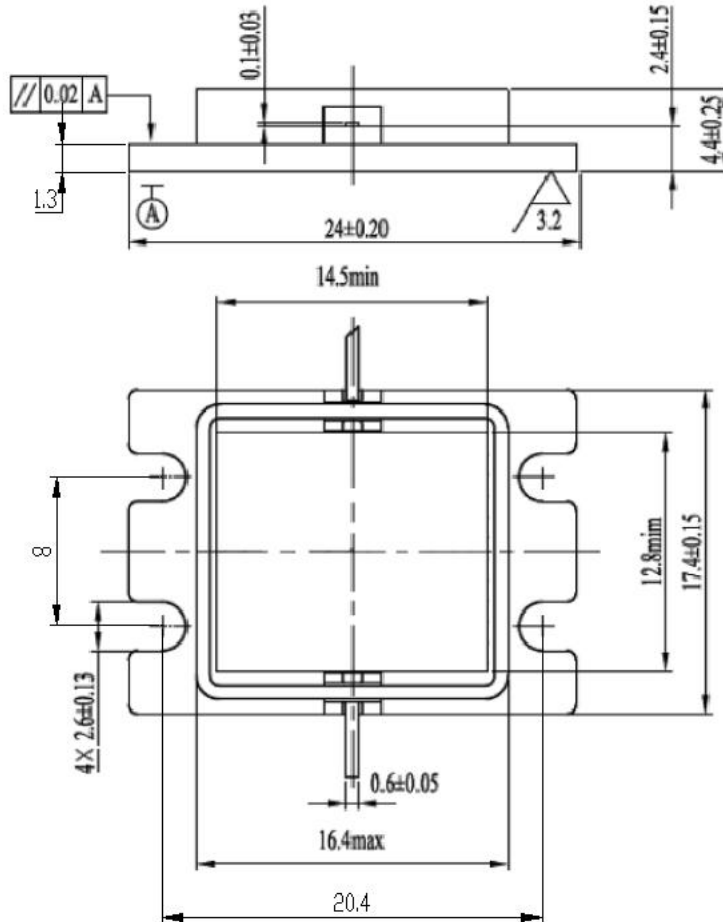
R_g:15Ω

r(radius)≈5.8mm(Rogers5880, 20mil)

ESD Level:

| | | |
|-----|-----------|-------|
| ESD | Class III | 2000V |
|-----|-----------|-------|

Outline:



Precautions for use:

- Pay attention to drying transportation and storage.
- Pay attention to anti-static during chip use and assembly, and wear grounding anti-static bracelet.
- When powering up, first apply grid power then add leakage.